Ina T Martin

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Angle-Resolved XPS Analysis and Characterization of Monolayer and Multilayer Silane Films for DNA Coupling to Silica. Langmuir, 2013, 29, 4057-4067.	3.5	89
2	Comparison of pulsed and downstream deposition of fluorocarbon materials from C3F8 and c-C4F8 plasmas. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 227-235.	2.1	53
3	Controlled Nitrogen Doping and Film Colorimetrics in Porous TiO ₂ Materials Using Plasma Processing. ACS Applied Materials & Interfaces, 2010, 2, 1743-1753.	8.0	52
4	Material quality requirements for efficient epitaxial film silicon solar cells. Applied Physics Letters, 2010, 96, 073502.	3.3	43
5	Ion effects on CF2 surface interactions during C3F8 and C4F8 plasma processing of Si. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 2168-2176.	2.1	40
6	Hot-wire chemical vapor deposition of epitaxial film crystal silicon for photovoltaics. Thin Solid Films, 2011, 519, 4545-4550.	1.8	38
7	Plasma Modification of PDMS Microfluidic Devices for Control of Electroosmotic Flow. Plasma Processes and Polymers, 2007, 4, 414-424.	3.0	30
8	Radical-surface interactions during film deposition: A sticky situation?. Pure and Applied Chemistry, 2006, 78, 1187-1202.	1.9	28
9	Pulsedâ€Plasmaâ€Induced Micropatterning with Alternating Hydrophilic and Hydrophobic Surface Chemistries. Plasma Processes and Polymers, 2008, 5, 129-145.	3.0	28
10	High-Resolution X-ray Photoelectron Spectroscopy of Mixed Silane Monolayers for DNA Attachment. ACS Applied Materials & Interfaces, 2011, 3, 3285-3292.	8.0	25
11	Mechanisms controlling the phase and dislocation density in epitaxial silicon films grown from silane below 800 A°C. Applied Physics Letters, 2010, 96, .	3.3	23
12	Doping of high-quality epitaxial silicon grown by hot-wire chemical vapor deposition near 700°C. Thin Solid Films, 2009, 517, 3496-3498.	1.8	21
13	Degradation of transparent conductive oxides: Interfacial engineering and mechanistic insights. Solar Energy Materials and Solar Cells, 2015, 143, 529-538.	6.2	19
14	Local Measurement of Janus Particle Cap Thickness. ACS Applied Materials & Interfaces, 2018, 10, 30925-30929.	8.0	18
15	Correlating ion energies and CF2 surface production during fluorocarbon plasma processing of silicon. Journal of Applied Physics, 2006, 100, 013301.	2.5	17
16	High rate hot-wire chemical vapor deposition of silicon thin films using a stable TaC covered graphite filament. Thin Solid Films, 2011, 519, 4585-4588.	1.8	14
17	Physics and chemistry of hot-wire chemical vapor deposition from silane: Measuring and modeling the silicon epitaxy deposition rate. Journal of Applied Physics, 2010, 107, 054906.	2.5	12
18	Organofunctional Silane Modification of Aluminum-Doped Zinc Oxide Surfaces as a Route to Stabilization. ACS Applied Materials & amp; Interfaces, 2017, 9, 17620-17628.	8.0	12

INA T MARTIN

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19	A combined CFD modeling and experimental study of pyrolytic carbon deposition. Diamond and Related Materials, 2016, 70, 173-178.	3.9	7
20	Dislocation-limited open circuit voltage in film crystal silicon solar cells. Applied Physics Letters, 2012, 101, 123510.	3.3	6
21	Degradation of transparent conductive oxides: mechanistic insights across configurations and exposures. , 2013, , .		4
22	Degradation of Transparent Conductive Oxides, and the Beneficial Role of Interfacial Layers. Materials Research Society Symposia Proceedings, 2013, 1537, 1.	0.1	4
23	Degradation Processes in Photovoltaic Cells. , 2019, , 97-118.		4
24	Quality and Growth Rate of Hot-wire Chemical Vapor Deposition Epitaxial Si Layers. Materials Research Society Symposia Proceedings, 2008, 1066, 1.	0.1	1
25	Interfacial modifiers for enhanced stability and reduced degradation of Cu(In,) Tj ETQq1 1 0.784314 rgBT /Overlo	ck 10 Tf 5	0 502 Td (C
26	Photovoltaic-quality silicon epitaxy by hot-wire CVD at glasscompatible temperatures. , 2009, , .		0
27	Epitaxial film silicon solar cells fabricated by hot wire chemical vapor deposition below 750°C. , 2009, , .		0
28	Decoupling the Effects of Interfacial Chemistry and Grain Size in Perovskite Stability. , 2021, , .		0